IN THE CLAIMS

Replace the indicated claims with:

A5 sub B1

1. (Amended) A semiconductor device, comprising:

a first conductive layer;

a first ball on said first conductive layer;

a second conductive layer spaced apart from said first conductive layer;

a second ball on said second conductive layer; and

a bonding wire connecting said first and second balls, wherein said second ball is formed by mechanically deforming said bonding wire.

2. (Amended) The semiconductor device according to claim 1, wherein said second ball is formed by bending said bonding wire on said second conductive layer.

3. (Amended) The semiconductor device according to claim 1, wherein said second ball is formed by curving said bonding wire on said second conductive layer.

A6

5. (Amended) The semiconductor device according to claim 1, comprising

a base;

a semiconductor element on said base with a die pad interposed between said semiconductor element and said base;

a sealing resin sealing said semiconductor element; and

an external terminal on a rear surface of said base, wherein

said first conductive layer includes a land on said base, and

said second conductive layer includes a bonding pad on said semiconductor element.

pad C1

6. (Amended) The semiconductor device according to claim 1, comprising:

a base;

first and second semiconductor elements mounted on said base with a die pad interposed between said base and said first and second semiconductor elements;

a sealing resin sealing said first and second semiconductor elements; and

an external terminal on a rear surface of said base, wherein

said first conductive layer includes a first bonding pad on said first semiconductor element, and

said second conductive layer includes a second bonding pad on said second semiconductor element.

7. (Amended) A method of manufacturing a semiconductor device, comprising, sequentially:

joining a first ball formed at a tip end of a bonding wire to a first conductive layer;

joining said bonding wire to a second conductive layer;

mechanically deforming said bonding wire on said second conductive layer, with said bonding wire joined to the second conductive layer; and

joining the portion of said bonding wire deformed to said second conductive layer.

8. (Amended) The method of manufacturing a semiconductor device according to claim 7, wherein mechanically deforming said bonding wire includes bending said bonding wire on said second conductive layer.

9. (Amended) The method of manufacturing a semiconductor device according to claim 7, wherein mechanically deforming said bonding wire includes curving said bonding wire on said second conductive layer.

10. (Amended) The method of manufacturing a semiconductor device according to claim 7, wherein

said bonding wire is held by a bonding tool; and

mechanically deforming said bonding wire includes mechanically deforming said bonding wire on said second conductive layer by moving said bonding tool with said bonding wire being joined to said second conductive layer.